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## **DUAL LOW VOLTAGE POWER AMPLIFIER**

### **■ GENERAL DESCRIPTION**

The NJM2076 is a dual power amplifier, which operates with 1.0V minimum supply voltage. The NJM2076 is suitable to small radio and head-phone of stereo and single BTL application.

### **■ FEATURES**

- BTL operation Po=90mW type.
- Minimum external components
- Headphone stereo Amp. with external transistors

Low Operation Voltage

(1.0V MIN.)

Low Operating Current

(4.7mA TYP.)

Package Outline

DIP8, DMP8

Bipolar Technology

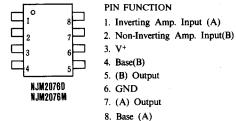
### **■ PIN CONFIGURATION**

### **■ PACKAGE OUTLINE**





NJM2876M



## ■ ABSOLUTE MAXIMUM RATINGS

(Ta=25℃)

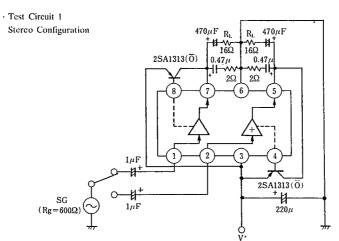
PARAMETER	SYMBOL	RATINGS	UNIT	
Supply Voltage	V+	4.5		
Maximum Input Signal	V <sub>IN</sub>	200	mVrms	
Power Dissipation	PD	(DIP 8) 500		
		(DMP 8) 500	mW	
Operating Temperature Range	Topr	-20~+75	r	
Storage Temperature Range	T <sub>stg</sub>	-40~+125	C	

### ■ ELECTRICAL CHARACTERISTICS

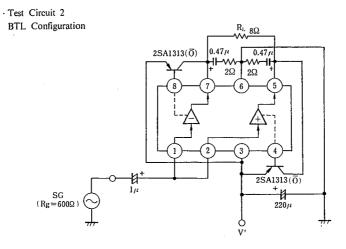
(Ta=25 $^{\circ}$ C, V<sup>+</sup>=1.5V)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Operating Current	I <sub>∞</sub>	Input: Open	_	4.7	7.0	mA
(I) Stereo Configuration (Test Circuit 1. R <sub>L</sub>	=16Ω)			<u></u>	1	
Voltage Gain	Av	V <sub>IN</sub> =10mVrms	26.5	28.0	29.5	dB
Max. Output Power	Poi	THD=10%(D, M-Type)	15	17.5	-	mW
	Po <sub>2</sub>	THD=10%, V <sup>+</sup> =1.0V	_	3	_	mW
Total Harmonic Distortion	THD	$P_O = 1 \text{mW} (126 \text{mVrms}/16\Omega)$		0.4	0.8	%
Output Noise Voltage	V <sub>NO1</sub>	Rg=0, A Curve		50	150	μV
Ripple Rejection Ratio	RR,	$Rg=0.f_R=1kHz, V_R=30mvrms$	25	35	_	dB
Input Resistance	R <sub>IN</sub>	, , ,	25	33	43	kΩ
Output Pin Voltage	Vo (DC)		0.62	0.70	0.77	v
(II) BTL Configuration (Test Circuit 2, R <sub>L</sub> =80	<b>1</b> )		<u>. J </u>			
Max. Output power	P <sub>O3</sub>	THD=10% (D,M-Type)	75	90	_	mW
	P <sub>O4</sub>	THD=10%. V+=1.0V(D, M-Type)	-	20	_	mW
Total Harmonic Distortion	THD <sub>2</sub>	$P_{\Omega} = 10 \text{mW} (283 \text{mVrms}/8\Omega)$	_	1.5	4.5	%
Output Noise Voltage	V <sub>NO2</sub>	Rg=0, A Curve	_	85	250	μV
Ripple Rejection Ratio	RR <sub>2</sub>	$Rg=0$ , $f_R=1kHz$ , $V_R=30mVrms$	20	25	_	dB
Voltage Difference between Two Output Pins	$\Delta V_0$ (DC)	,	-	_	50	mV
		L	1		l	

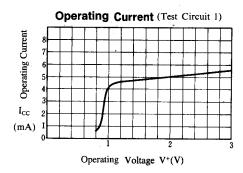
### **■ TEST CIRCUIT**

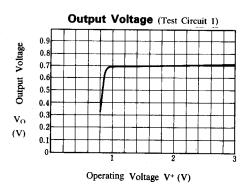


2SA1313(Ö): h<sub>FF</sub>=115~125 (Ic=100mA)

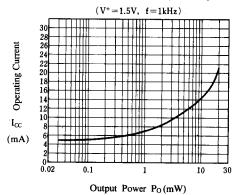


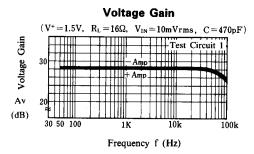
### ■ TYPICAL CHARACTERISTICS



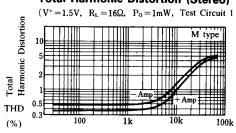


## **Operating Current (Stereo)**



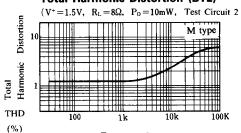


### **Total Harmonic Distortion (Stereo)**



Frequency f (Hz)

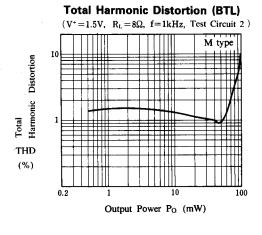
### Total Harmonic Distortion (BTL)



Frequency f (Hz)

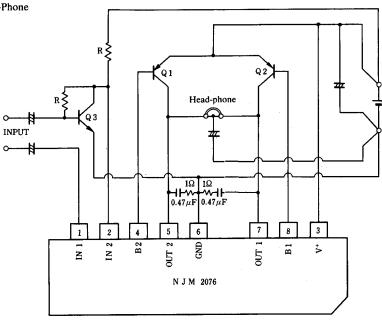
### **■ TYPICAL CHARACTERISTICS**

# Total Harmonic Distortion (Stereo) (V+=1.5V, R<sub>L</sub>=16Q, f=1kHz, Test Circuit 1) M type 10 NH type 10 NH

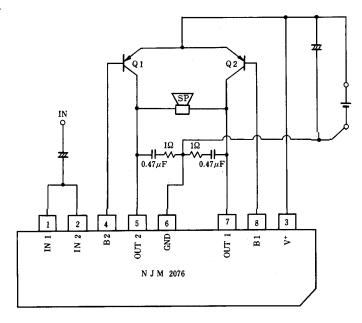


### **■ TYPICAL APPLICATION**

1. For Stereo Head-Phone



### 2. BTL Amp. for Speaker



### **■ NOTICE**

### (1) External PNP Transistor

Maximum output power becomes large with low saturation voltage transistor, and so select transistor of low saturation. Saturation Voltage: less than 0.1V (Ic=100mA.  $I_B=10mA$ ).  $h_{FE}$ : 120

### (2) External Frequency Compensation

Recommend tantalum capacitor with low tan $\delta$  (less than 0.25 at f=10kHz) and 1 $\Omega$  resistor. Stable with large capacitor of less high frequency distortion and worse tan $\delta$ . For example:  $1\mu F$ , tan $\delta \leq 0.6$ 

### (3) Layout on PCB

Be careful to get maximum output power and low distortion set.

DIP/DMP: Signal ground has to be close to IC ground pin. Impedance of ground line must be low.

# **NJM2076**

# **MEMO**

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